April 2007



SEMICONDUCTOR

FFPF10H60S Hyperfast 2 Rectifier

Features

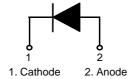
- High Speed Switching (t_{rr}=25ns(Typ.) @ I_F=10A)
- High Reverse Voltage and High Reliability
- Avalanche Energy Rated
- Low Forward Voltage(V_F=2.1V(Typ.) @ I_F=10A)

Applications

- General Purpose
- Switching Mode Power Supply
- · Free-wheeling diode for motor application
- Power switching circuits

Pin Assignments





10A, 600V Hyperfast 2 Rectifier

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tors.

The FFPF10H60S is hyperfast2 rectifier (t_{rr} =25ns(Typ.) @ I_F=10A). it has half the recovery time of ultrafast rectifier and is

silicon nitride passivated ion-implanted epitaxial planar con-

This device is intended for use as freewheeling/clamping rectifiers in a variety of switching power supplies and other power

swithching applications. Its low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power

switching circuits reducing power loss in the switching transis-

1. Cathode 2. Anode

Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{RRM}	Peak Repetitive Reverse Voltage	600	V
V _{RWM}	Working Peak Reverse Voltage	600	V
V _R	DC Blocking Voltage	600	V
I _{F(AV)}	Average Rectified Forward Current @ $T_C = 85 \degree C$	10	А
I _{FSM}	Non-repetitive Peak Surge Current 60Hz Single Half-Sine Wave	100	А
T _{J,} T _{STG}	Operating Junction and Storage Temperature	- 65 to +150	°C

Thermal Characteristics T_C = 25°C unless otherwise noted

Symbol	Parameter	Мах	Units
$R_{ extsf{ heta}JC}$	Maximum Thermal Resistance, Junction to Case	3.4	°C/W

Package Marking and Ordering Information

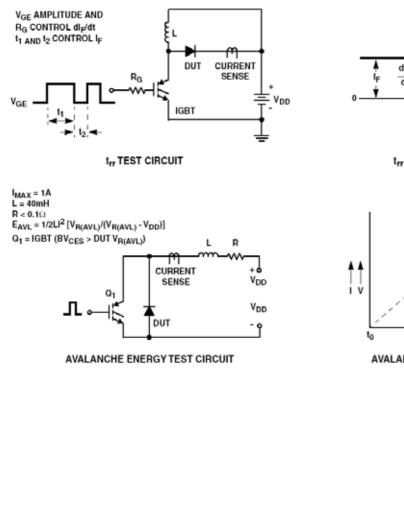
F10H60S FFPF10H60STU TO-220F - 50	Device Mark	ing [Device	Package	Reel Size	Tape W	/idth	Quantity
	F10H60S	FFP	T10H60STU	TO-220F	-	-		50

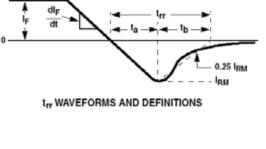
Parameter	Conditions		Min.	Тур.	Max	Units
V _{FM} ¹	I _F = 10A I _F = 10A	T _C = 25 °C T _C = 125 °C	-	2.1	2.5 2.2	V V
I _{RM} ¹	$V_{R} = 600V$ $V_{R} = 600V$	T _C = 25 °C T _C = 125 °C	-	-	1 2	mA mA
t _{rr}	$ I_{F} = 1A, di/dt = 100A/\mu s, V_{CC} = 30V \\ I_{F} = 10A, di/dt = 50A/\mu s, V_{CC} = 390V \\ I_{F} = 10A, di/dt = 200A/\mu s, V_{CC} = 390V $	$T_{C} = 25 °C$ $T_{C} = 25 °C$ $T_{C} = 25 °C$ $T_{C} = 25 °C$	- - -	- 25 21	35 40 -	ns ns ns
t _a t _b Q _{rr}	I _F =10A, di/dt = 50A/μs, V _{CC} = 390V	$T_{C} = 25 °C$ $T_{C} = 25 °C$ $T_{C} = 25 °C$ $T_{C} = 25 °C$	- - -	15 10 9.0		ns ns nC
W _{AVL}	Avalanche Energy (L = 40mH)	•	20	-	-	mJ

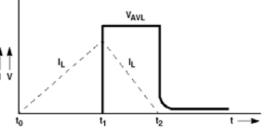
Notes:

1. Pulse : Test Pulse width = $300\mu s$, Duty Cycle = 2%

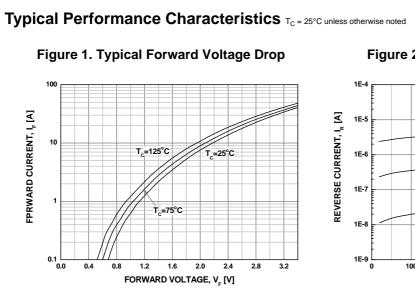
Test Circuit and Waveforms

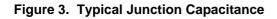






AVALANCHE CURRENT AND VOLTAGE WAVEFORMS





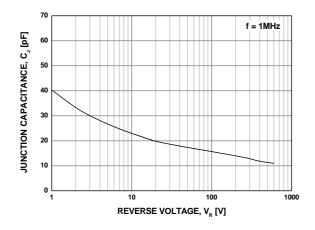


Figure 5. Typical Reverse Recovery Current

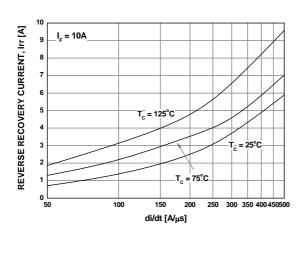


Figure 2. Typical Reverse Current

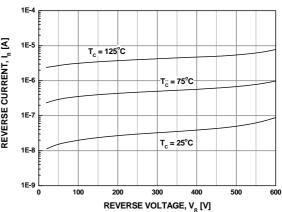


Figure 4. Typical Reverse Recovery Time

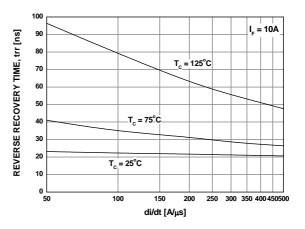
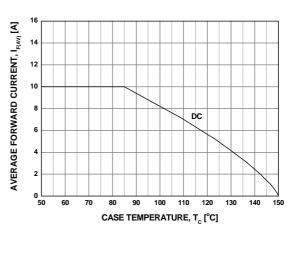
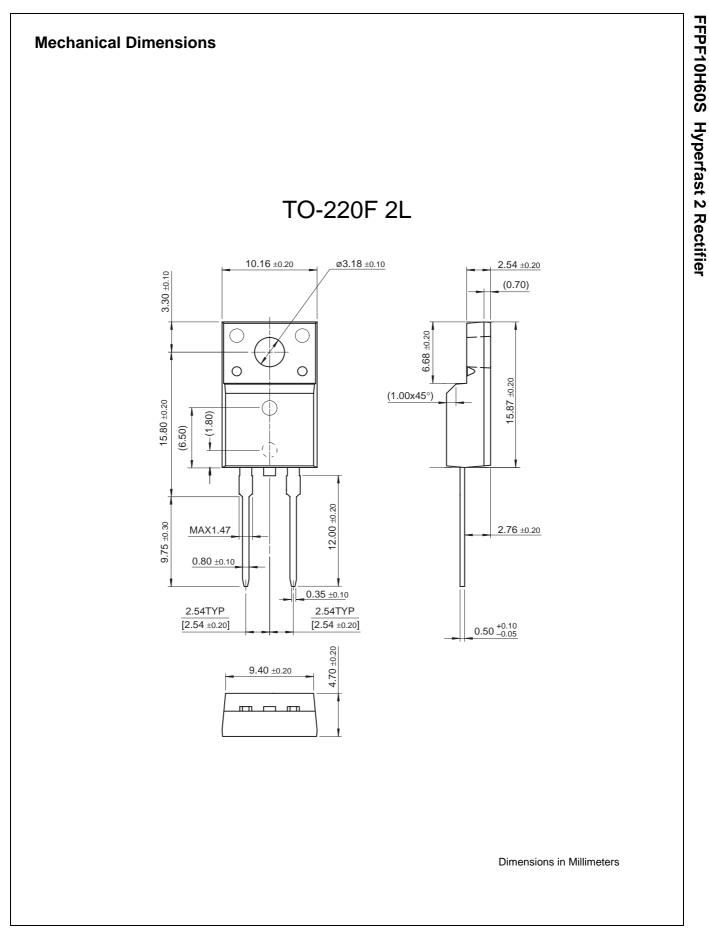


Figure 6. Forward Current Deration Curve







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CTL™	MICROCOUPLER™	QT Optoelectronics [™]	TinyLogic [®]
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E ² CMOS™	MSX™	RapidConnect™	TinyWire™
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EnSigna™	OCX™	SMART START™	µSerDes™
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